

MINIATURIZED MODULES FOR 5G & AUTOMOTIVE SYSTEMS

- High-end build up PCB
- Fine lines and spacing
- Miniaturized PCBs with reduced thickness
- Narrow pitch BGA and CSP fan-out

- Low-inductivity material,
- Low-inductivity orthotropic material,
- Low thermal expansion material
- Warpage measurements

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the AT&S booth.
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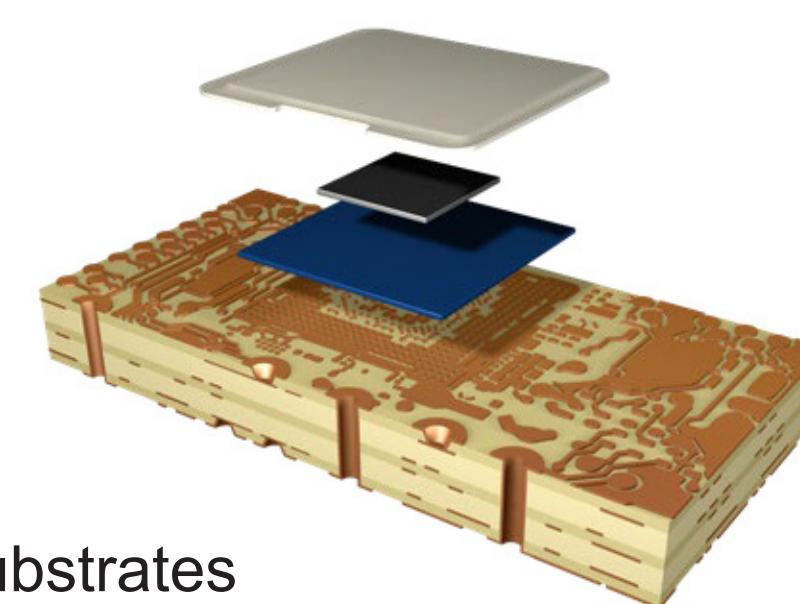
HDI Boards, SiP Modules, IC Substrates



HDI Boards,
40/40 µm



SiP/Modules
25/25 µm



IC-Substrates
10/10 µm

Line / Space (µm)

Applications:

- Mobile devices, imaging devices
- Consumer electronics
- ADAS computing
- Storage

Benefits:

- Miniaturization
- High data rates
- Short lines
- Adaptable to different requirements

Applications:

- V2X communication
- Connectivity modules
- Power modules
- Computing modules

Benefits:

- System size reduction
- System cost reduction
- Easy integration (Plug & Play)
- Reduced time to market

Applications:

- Data centres, microservers, 5G base stations
- Server & cloud computing, 3D sensing module
- High performance computers
- Notebook and 2-in-1-devices

Benefits:

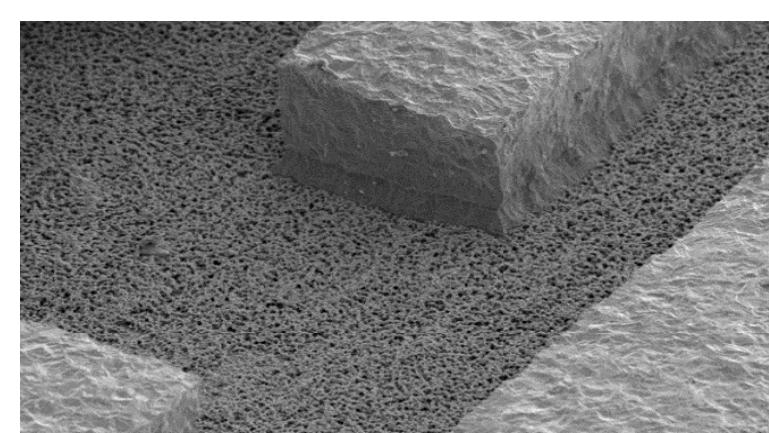
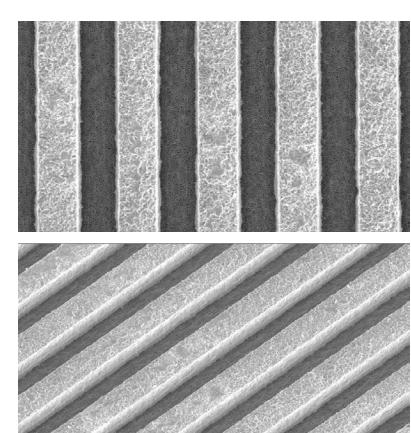
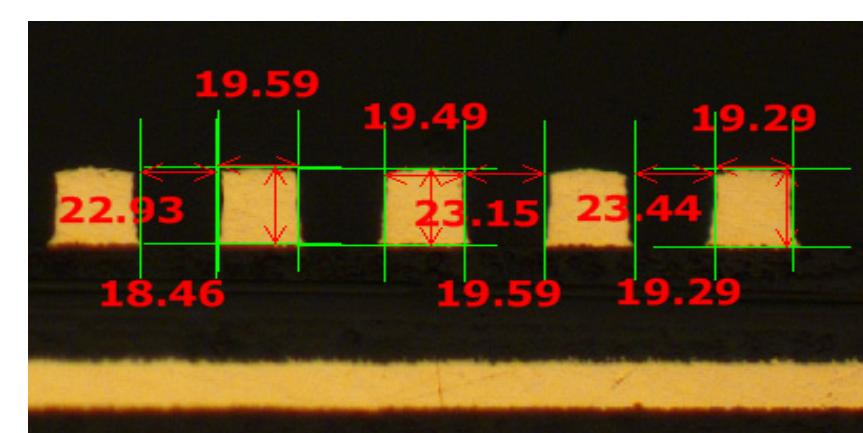
- High performance and reliability
- Flexible structure
- Can be adapted for many applications

HDI/mSAP/SAP capability

Technology	Subtractive	mSAP	IC-Substrate
Status	Mass production available	Mass production available	Mass production available
Laser pad size	110 µm	90 µm	77 µm
Line width / spacing	@Cu=15 µm	35/35 µm 30/40 µm	25/25 µm (MP) 20/20 µm (Sample)
	@Cu=30 µm	40/60 µm	-
Line geometry			
Min. copper thickness	10 µm	12 µm	15 µm
Min. dielectric thickness	20 µm	20 µm	25 µm
Min. soldermask thickness	10 µm		18 µm
Low Dk / Df material	Dk=3.4 / Df=0.004		Dk=3.36 / Df=0.0051 at 20GHz
Technology combination	Coreless, Laser trench, 2.5DC, 2.5DR, ECP		-

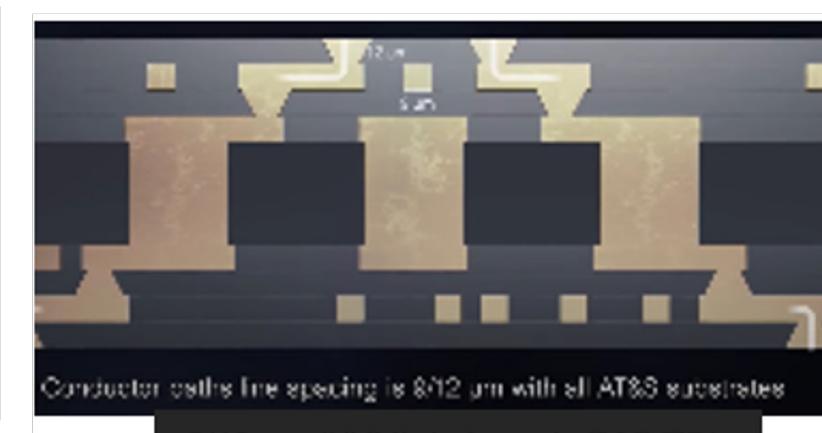
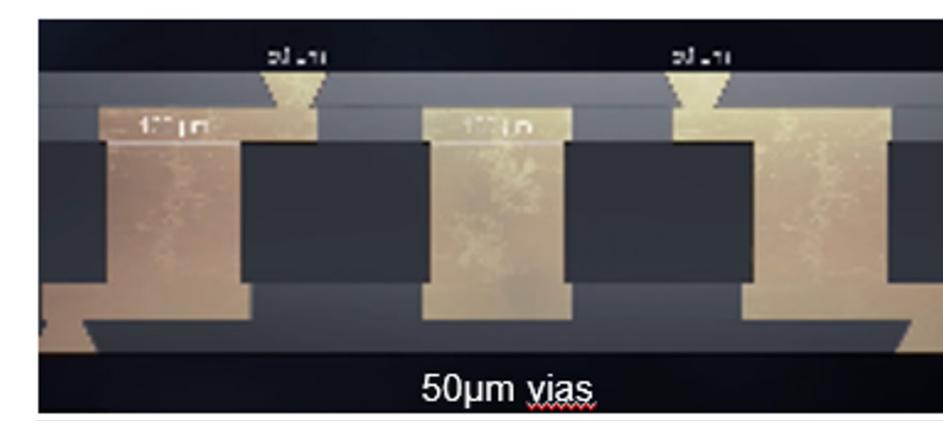
Cross section

Cross section (mSAP on outer layer)



Standard coreless substrate

Cross section (L/S 9/12 µm SAP)



Conductor voids free spacing > 0.12 µm with sl AT&S substrates

9/12 µm (HVM), below – in R&D/TDI